















ESD

TVS

MOS

LDO

Diode

Sensor

DC-DC

Product Specification

Domestic Part Number	BAT54J
Overseas Part Number	BAT54J
▶ Equivalent Part Number	BAT54J





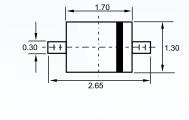
Schottky Barrier Diode

Features

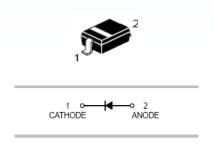
- ♦ Very samll conduction losses.
- Negligible switching losses.
- ♦ Low forward voltage drop.
- ♦ Surface mount device.

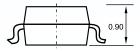
Applications

- ♦ Schottky barrier diodes.
- Single and double diodes with different pining are available.



SOD-323





Dimensions in inches and (millimeters)

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	Limits	Unit
Peak Repetitive reverse voltage	V _{RRM}	30	V
Forward continuous current	I _F	0.3	А
Surge non repetitive forward current tp=10ms	I _{FSM}	1	А
Power Dissipation	P _d	230	mW
Thermal resistance, junction to ambient air	R _{θjA}	550	°C/W
Junction temperature	T _j	150	$^{\circ}$
Storage temperature range	T _{stg}	-65-150	$^{\circ}$



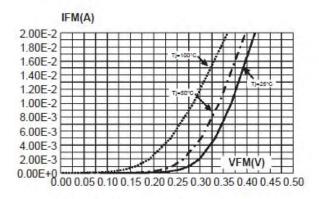
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward voltage	V _{F1}	I _F =0.1mA			240	mV
	V_{F2}	I _F =1.0mA			320	mV
	V_{F3}	I _F =10mA			400	mV
	V_{F4}	I _F =30mA			500	mV
	V_{F5}	I _F =100mA			900	mV
Reverse leakage current	I _R	V _R =30V T _j =25℃			1	μΑ
		V _R =30V T _j =100 ℃			100	μΑ
Reverse recovery time	t _{rr}	I _F =10mA,I _R =10mA	5		5.0	ns
Reverse recovery time		to 1mA R_L =100 Ω				
Junction capacitance	CJ	V _R =1.0V,f=1.0MHz			10	pF

TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Fig. 1-1: Forward voltage drop versus forward current (typical values, low level).

Fig. 1-2: Forward voltage drop versus forward current (typical values, high level).



1E-3

1E-1

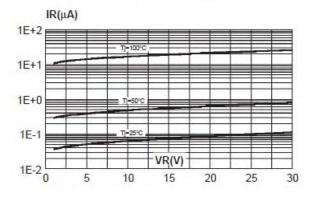
VFM(V)

1E-3

0.0 0.1 0.2 0.3 0.4 0.5 0.6 0.7 0.8 0.9 1.0 1.1

Fig. 2: Reverse leakage current versus reverse voltage applied (typical values).

Fig. 3: Reverse leakage current versus junction temperature.



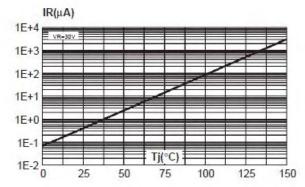




Fig. 4: Junction capacitance versus reverse voltage applied (typical values).

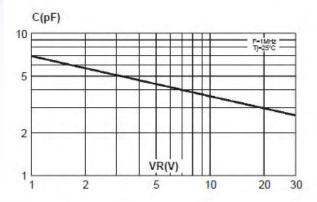


Fig. 5: Relative variation of thermal impedance junction to ambient versus pulse duration (epoxy FR4 with recommended pad layout, e(Cu)=35μm)

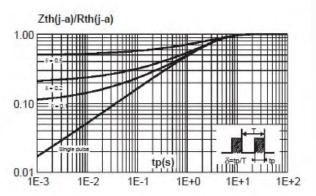
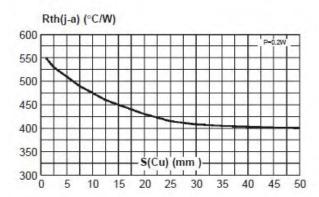


Fig. 6: Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board FR4, copper thickness: 35μm.)



PACKAGE	SPQ/PCS	CARTON SPQ/PCS	CARTON SIZE/CM	CARTON GW/KG	CARTON NW/KG
SOD-323	3000/REEL	180000	45X45X23	9.00	8.00



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